

AN 1997-122301 [12] WPIX Full-text

DNN N1997-100597 DNC C1997-039525

TI **Measurement of exhaust gas from internal combustion engine -**
includes using heated metal oxide semiconductor changing resistance with
oxygen concentration.

DC E36 H06 J04 L03 S02 S03 X22

PA (NITS) NGK SPARK PLUG CO LTD

CYC 1

PI JP--09005273 A 19970110 (199712)* 29p G01N-027-12 <--

ADT JP--09005273 A 1995JP-0176668 19950619

PRAI 1995JP-0176668 19950619

IC ICM G01N-027-12

AB JP 09005273 A UPAB: 19970320

A gas sensor (46) comprises a metallic oxide semiconductor the resistance value of which is changed according to oxygen concn; and a heater (75) arranged near the metallic oxide semiconductor. By measuring the resistance value of the metallic oxide semiconductor by applying an AC voltage on the metallic oxide semiconductor, the gas component concn in exhaust gas is measured.

ADVANTAGE - Deterioration due to migration of a metallic oxide semiconductor in high temp gas does not occur.

Dwg.5/32

FS CPI EPI

FA AB; GI; DCN

MC CPI: E11-Q03J; H06-C04; J04-C04; L03-E05C; L03-H05

EPI: S02-J01A; S03-E02A; X22-A05B